

N-channel 100 V, 0.065 Ω typ., 4 A STripFET™ II Power MOSFET in SO-8 package

Datasheet – production data

Features

Order code	V _{DS}	R _{DS(on)} max	I _D
STS4NF100	100 V	0.070 Ω	4 A

- Exceptional dv/dt capability
- 100 % avalanche tested
- Application oriented characterization

Applications

- Switching applications

Description

This Power MOSFET has been developed using STMicroelectronics' unique STripFET process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

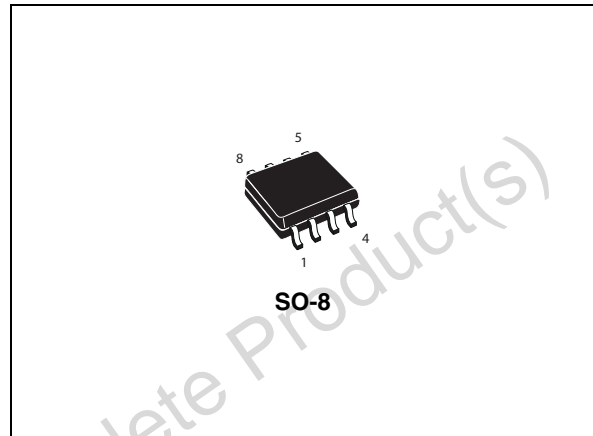


Figure 1. Internal schematic diagram

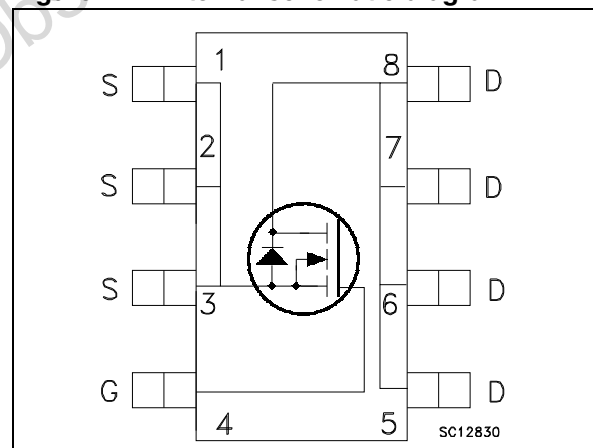


Table 1. Device summary

Order code	Marking	Package	Packaging
STS4NF100	4NF100	SO-8	Tape and reel

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Obsolete Product(s) - Obsolete Product(s)

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate- source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	4	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	2.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	16	A
P_{TOT}	Total dissipation at $T_{amb} = 25^\circ\text{C}$	2.5	W
T_J	Max. operating junction temperature	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature		$^\circ\text{C}$

1. Pulse width limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thj-a}	Thermal resistance junction-ambient max ⁽¹⁾	50	$^\circ\text{C}/\text{W}$

1. Mounted on FR-4 board (t 10 sec.)

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown voltage	I _D = 250 μA, V _{GS} = 0	100			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = 100 V V _{DS} = 100 V, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 20 V			±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 2 A		0.065	0.070	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 2 A	-	10		S
C _{iss}	Input capacitance		-	870		pF
C _{oss}	Output capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0	-	125		pF
C _{rss}	Reverse transfer capacitance		-	52		pF
Q _g	Total gate charge	V _{DD} = 80 V, I _D = 4 A, V _{GS} = 10 V	-	30	41	nC
Q _{gs}	Gate-source charge		-	6		nC
Q _{gd}	Gate-drain charge		-	10		nC

1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)} t _r	Turn-on delay time rise time	V _{DD} = 50 V, I _D = 4 A, R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 14)	-	58 45	-	ns ns
t _{d(off)} t _f	Turn-off delay time fall time	V _{DD} = 50 V, I _D = 4 A R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 14)	-	49 17	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		4	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		16	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 4 \text{ A}, V_{GS} = 0$	-		1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 4 \text{ A}, V_{DD} = 30 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s},$ $T_j = 150 \text{ }^\circ\text{C}$ (see Figure 15)	-	100		ns
Q_{rr}	Reverse recovery charge			375		nC
I_{RRM}	Reverse recovery current			7.5		A

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

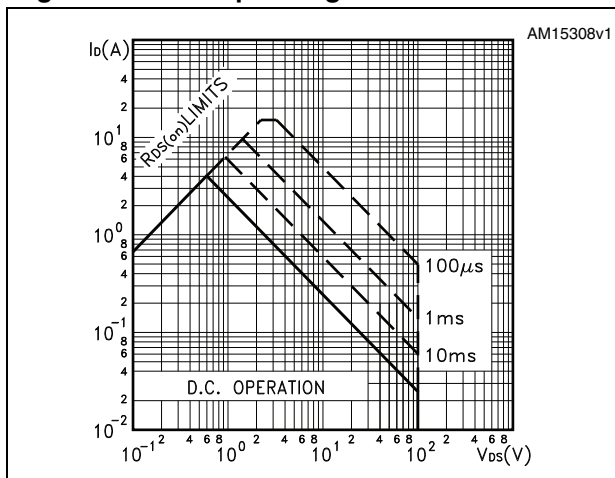


Figure 3. Thermal impedance

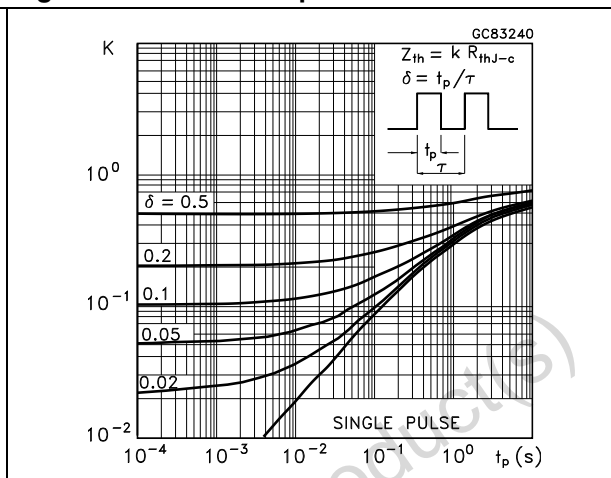


Figure 4. Output characteristics

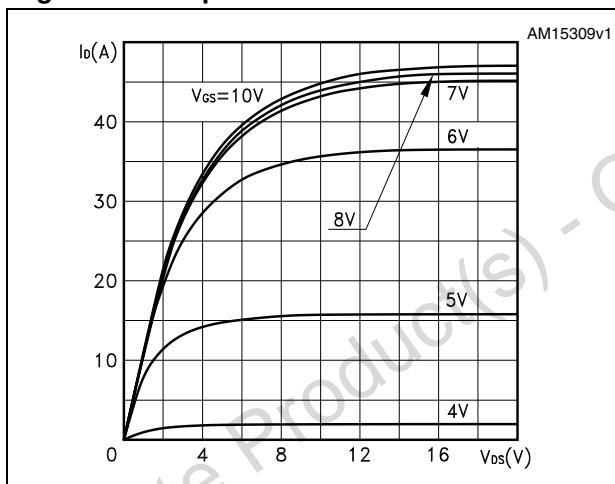


Figure 5. Transfer characteristics

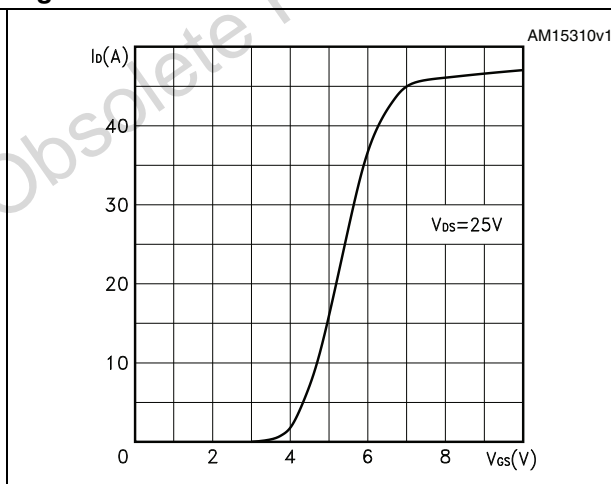


Figure 6. Transconductance

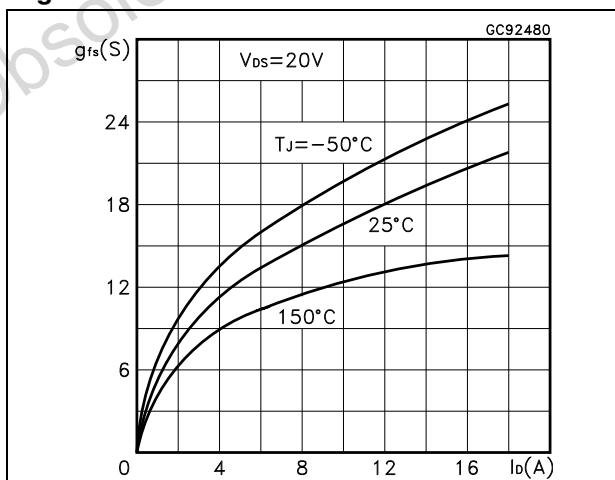


Figure 7. Static drain-source on-resistance

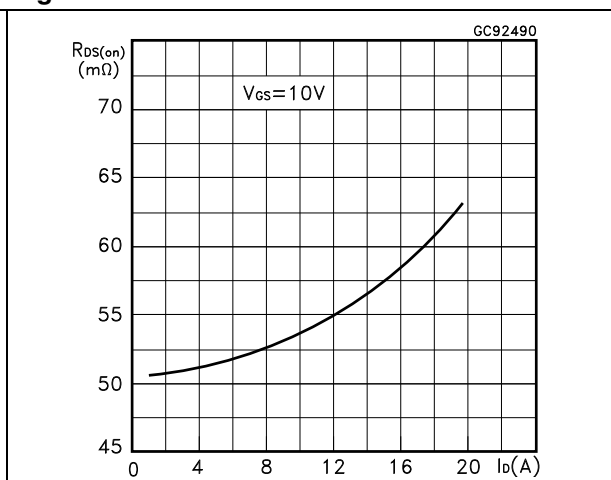


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

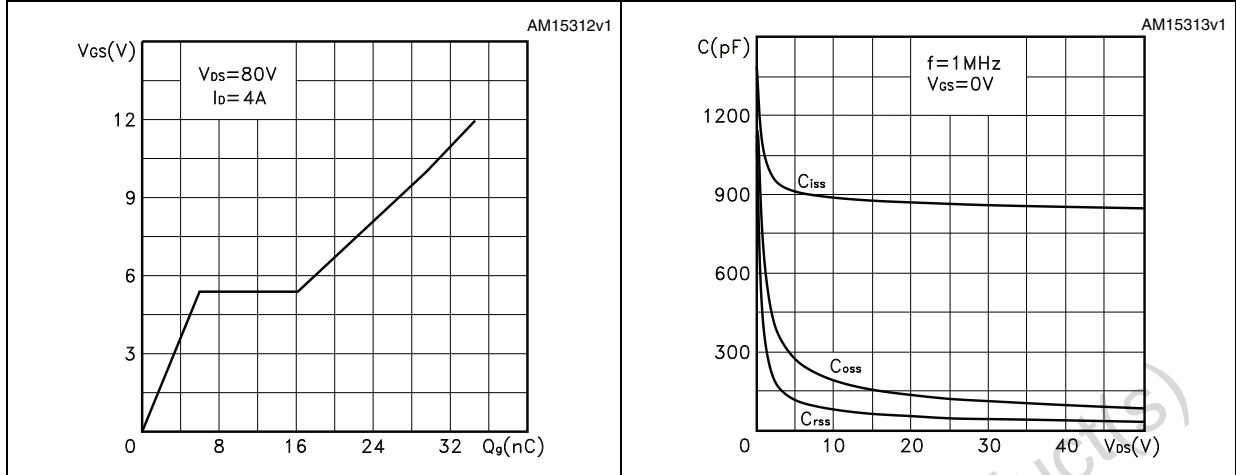


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on-resistance vs temperature

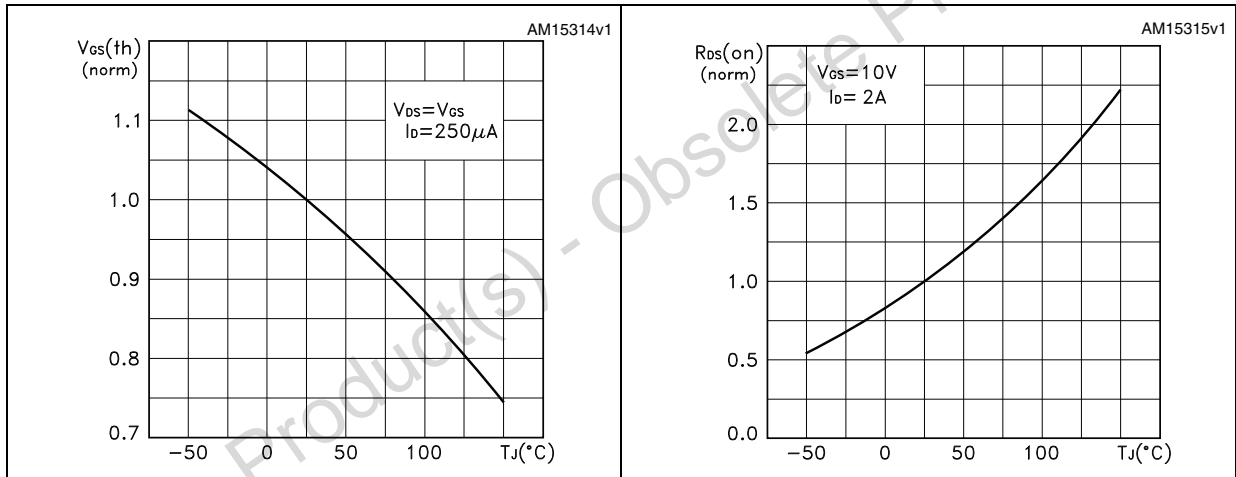
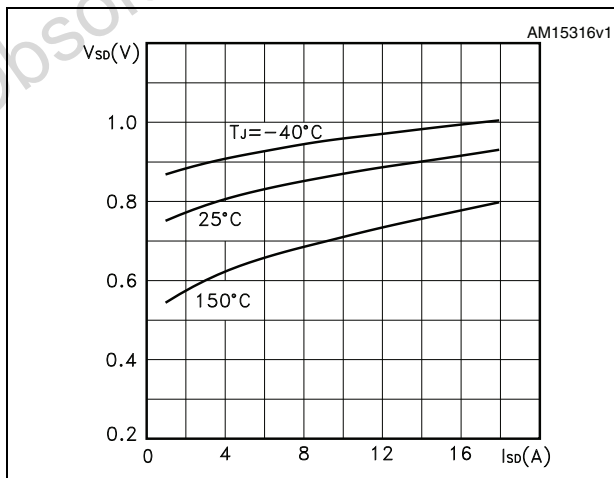


Figure 12. Source-drain diode forward characteristics



3 Test circuit

Figure 13. Switching times test circuit for resistive load

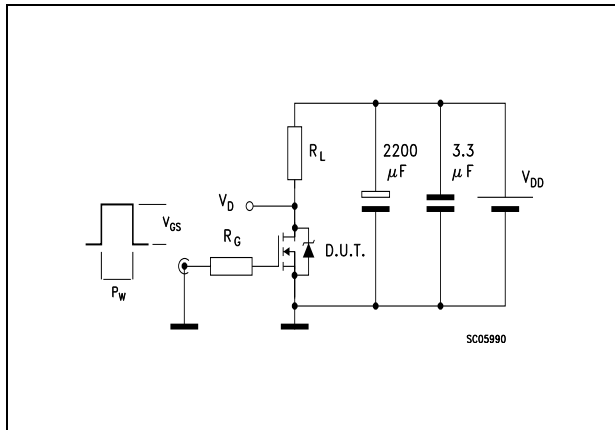


Figure 14. Gate charge test circuit

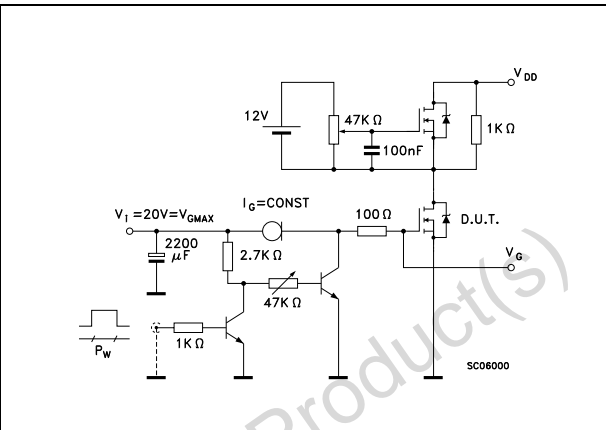


Figure 15. Test circuit for inductive load switching and diode recovery times

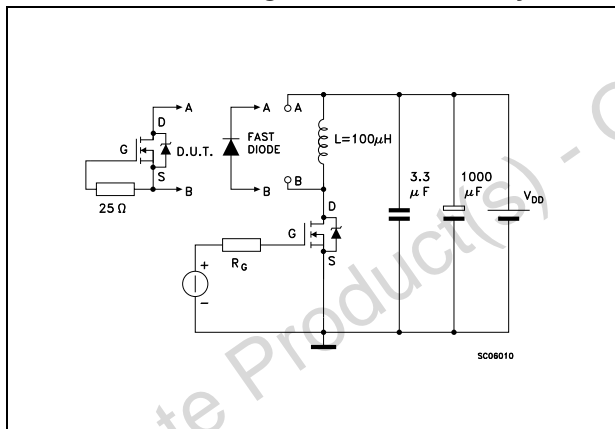


Figure 16. Unclamped Inductive load test circuit

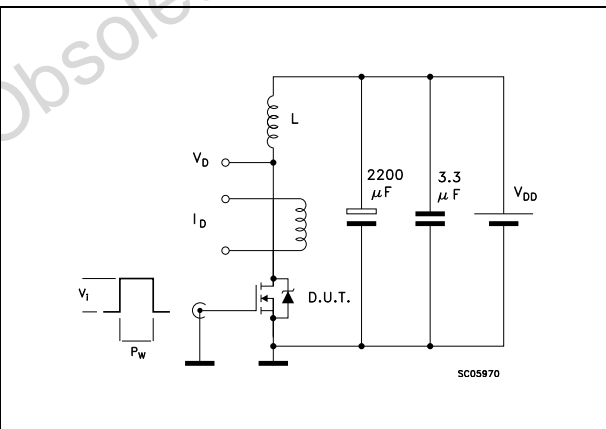


Figure 17. Unclamped inductive waveform

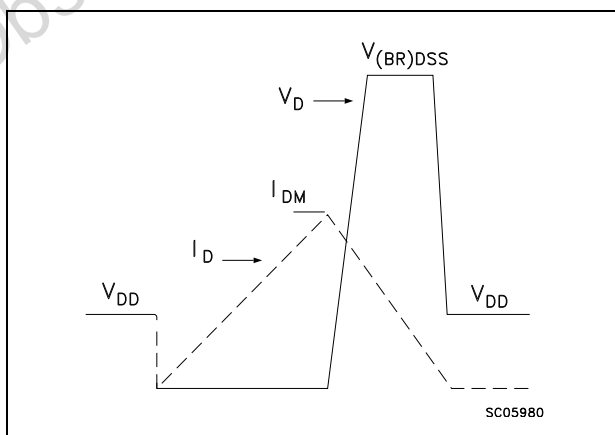
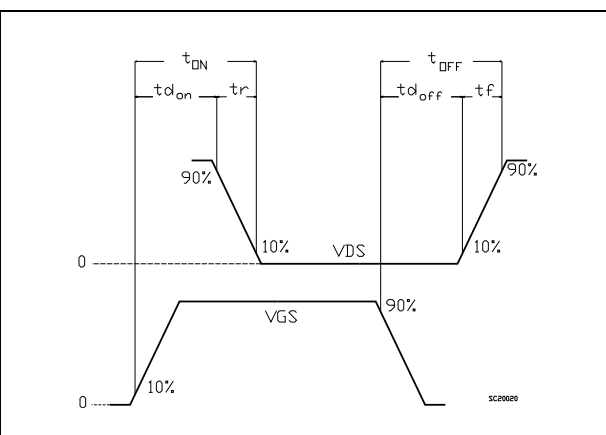


Figure 18. Switching time waveform



4 Package mechanical data

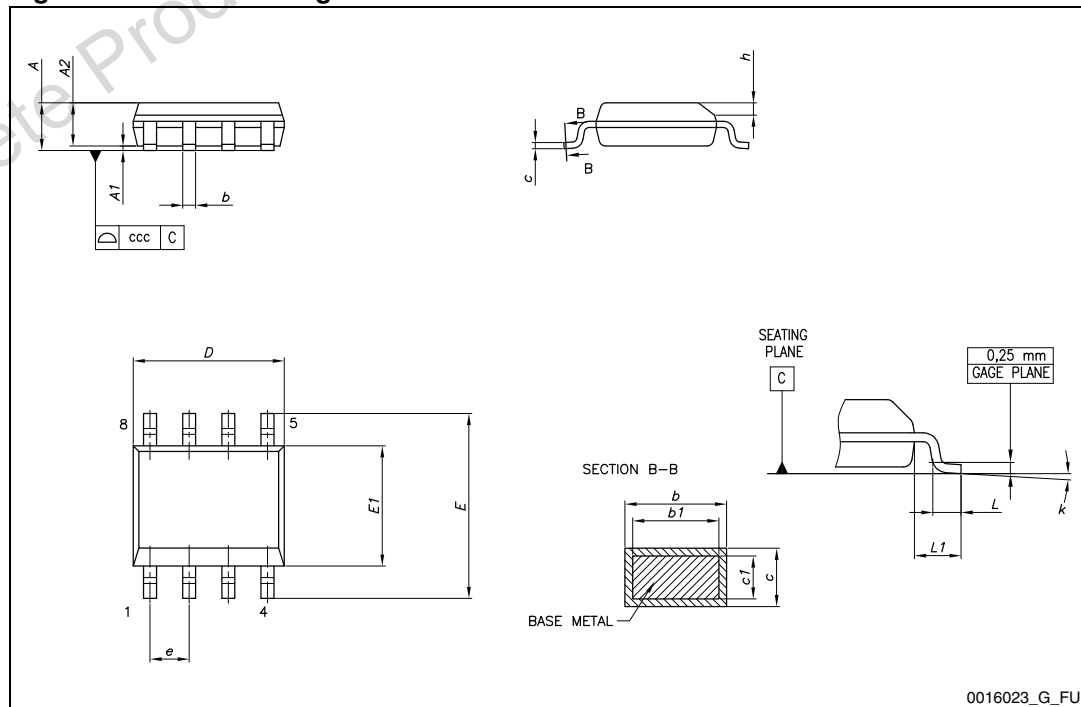
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Table 8. SO-8 mechanical data

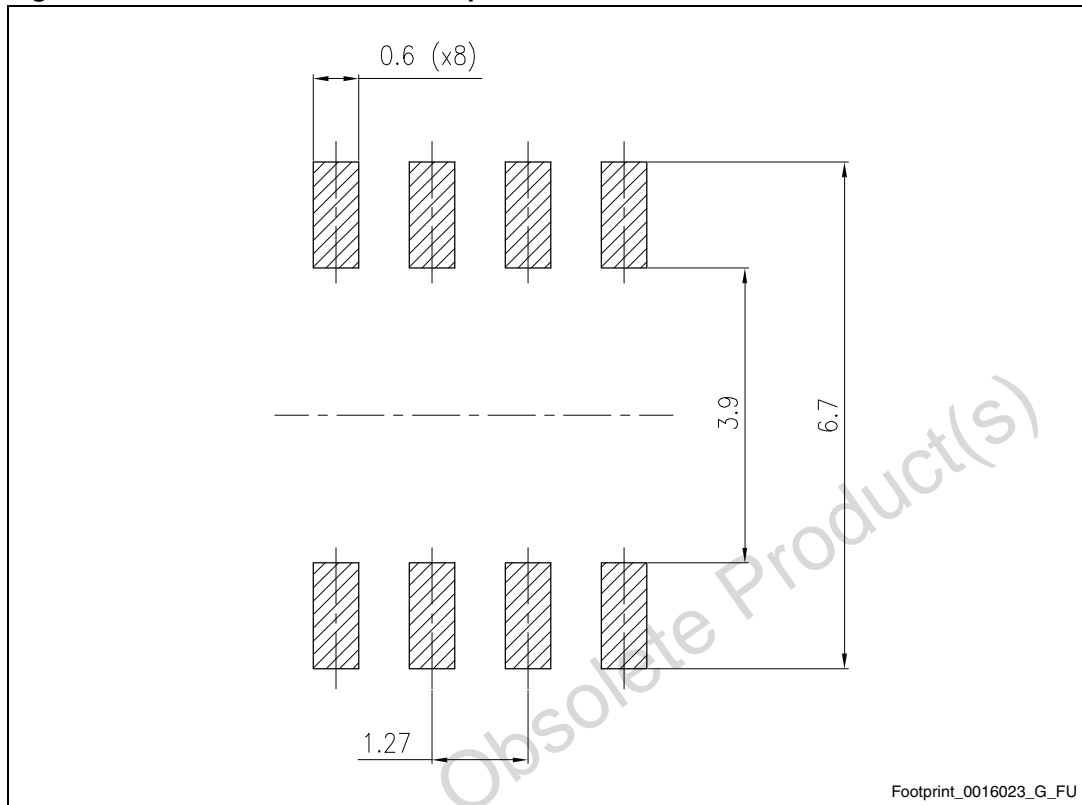
Dim.	mm		
	Min.	Typ.	Max.
A			1.75
A1	0.10		0.25
A2	1.25		
b	0.31		0.51
b1	0.28		0.48
c	0.10		0.25
c1	0.10		0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e		1.27	
h	0.25		0.50
L	0.40		1.27
L1		1.04	
L2		0.25	
k	0°		8°
ccc			0.10

Figure 19. SO-8 drawing



0016023_G_FU

Figure 20. SO-8 recommended footprint^(a)



a. All dimensions are in millimeters.

5 Revision history

Table 9. Revision history

Date	Revision	Changes
11-Sep-2006	1	First release
15-Nov-2006	2	The document has been reformatted
26-Jan-2007	3	Typo mistake on Table 3 .
19-Nov-2012	4	Changed: marking in cover page

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